

# GSM4248W

## 20V N-Channel Enhancement Mode MOSFET

### Product Description

GSM4248W, N-Channel enhancement mode MOSFET, uses Advanced Trench Technology to provide excellent  $R_{DS(ON)}$ , low gate charge.

These devices are particularly suited for low voltage power management, and low in-line power loss are needed in commercial industrial surface mount applications.

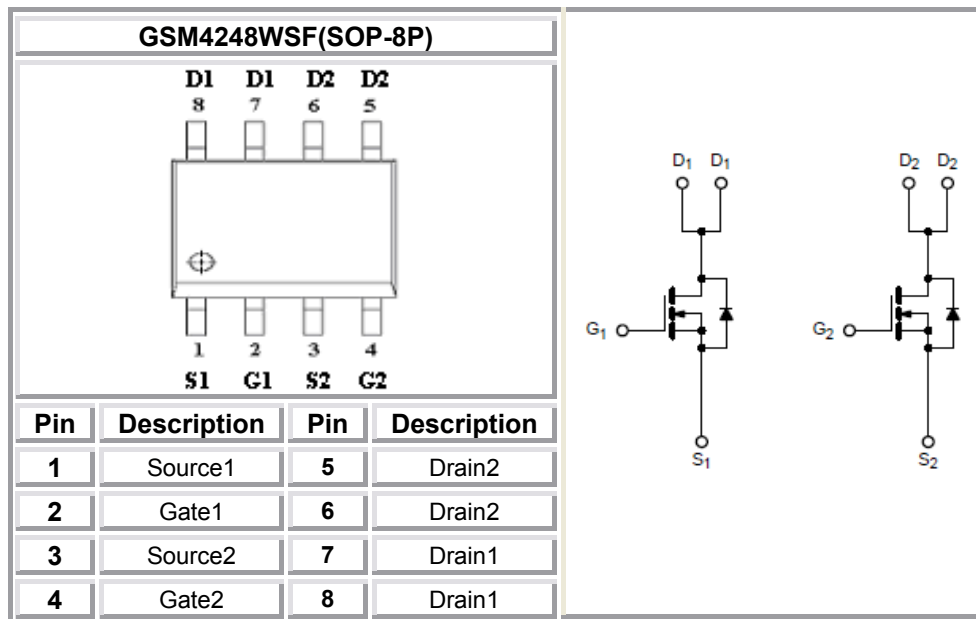
### Features

- 20V/6.0A,  $R_{DS(ON)}=28m\Omega@V_{GS}=4.5V$
- 20V/5.0A,  $R_{DS(ON)}=32m\Omega@V_{GS}=2.5V$
- 20V/4.0A,  $R_{DS(ON)}=42m\Omega@V_{GS}=1.8V$
- Super high density cell design for extremely low  $R_{DS(ON)}$
- SOP-8P package design

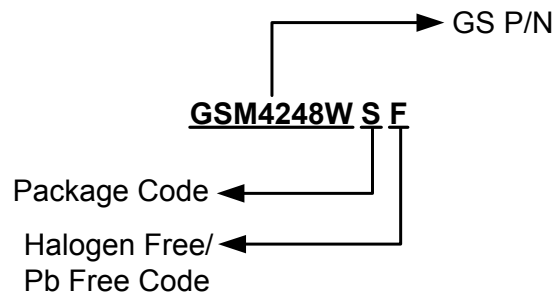
### Applications

- Low Current DC/DC Conversion
- Load Switch
- CCFL Inverter
- Power Management in Notebook Computer

### Packages & Pin Assignments

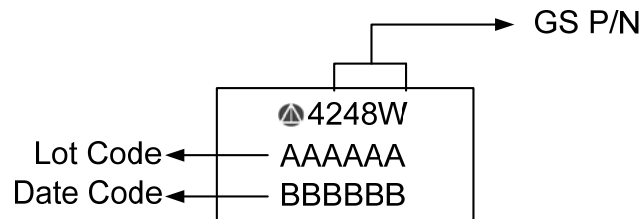


## Ordering Information



Part Number	Package	Quantity Reel
GSM4248WSF	SOP-8P	2500 PCS

## Marking Information



## Absolute Maximum Ratings

(T<sub>A</sub>=25°C unless otherwise noted)

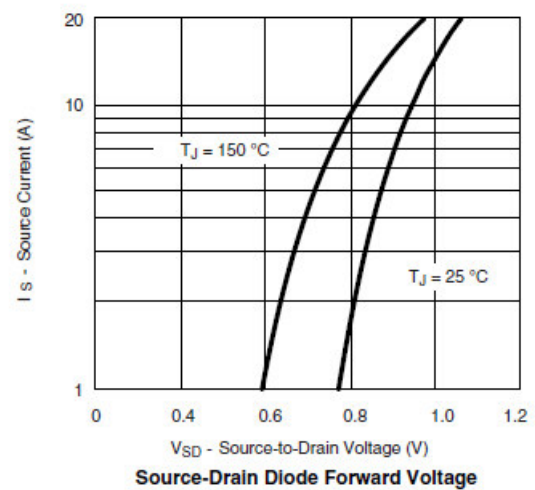
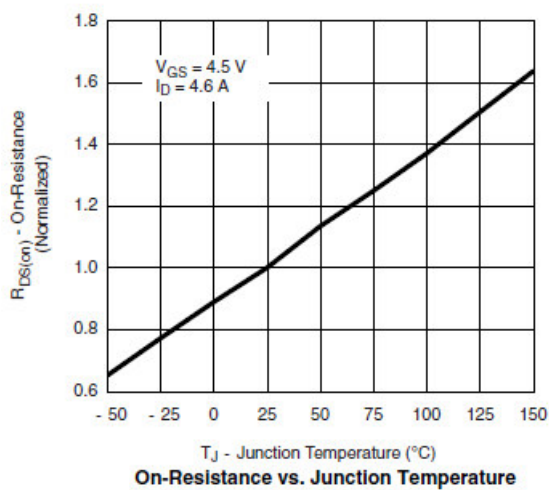
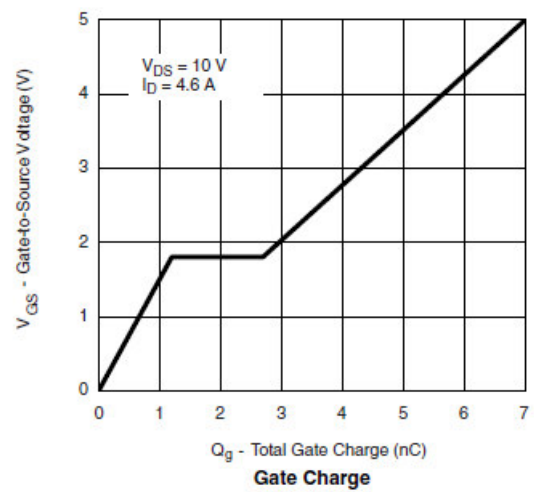
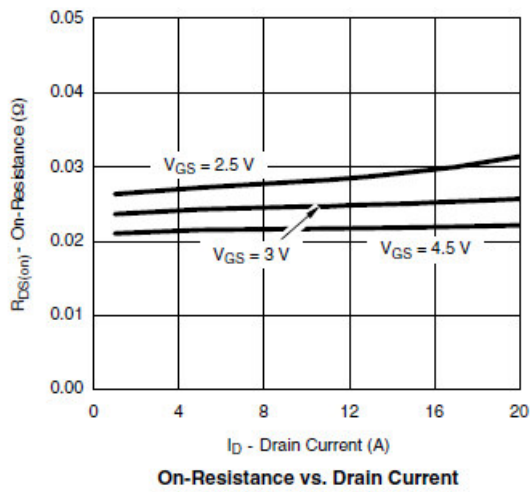
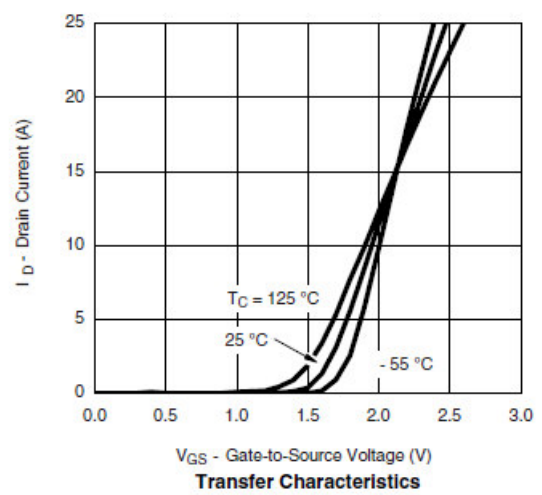
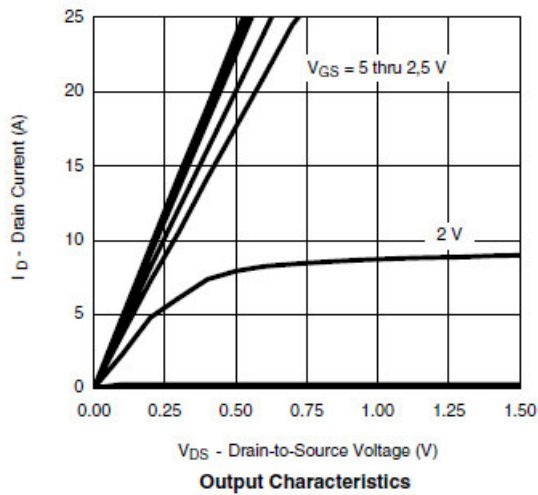
Symbol	Parameter	Typical	Unit
V <sub>DSS</sub>	Drain-Source Voltage	20	V
V <sub>GSS</sub>	Gate-Source Voltage	±12	V
I <sub>D</sub>	Continuous Drain Current(T <sub>J</sub> =150°C)	T <sub>A</sub> =25°C	6.0
		T <sub>A</sub> =70°C	4.0
I <sub>DM</sub>	Pulsed Drain Current	20	A
I <sub>S</sub>	Continuous Source Current(Diode Conduction)	1.5	A
P <sub>D</sub>	Power Dissipation	T <sub>A</sub> =25°C	2.8
		T <sub>A</sub> =70°C	1.8
T <sub>J</sub>	Operating Junction Temperature	150	°C
T <sub>STG</sub>	Storage Temperature Range	-55/150	°C
R <sub>θJA</sub>	Thermal Resistance-Junction to Ambient	62.5	°C/W

## Electrical Characteristics

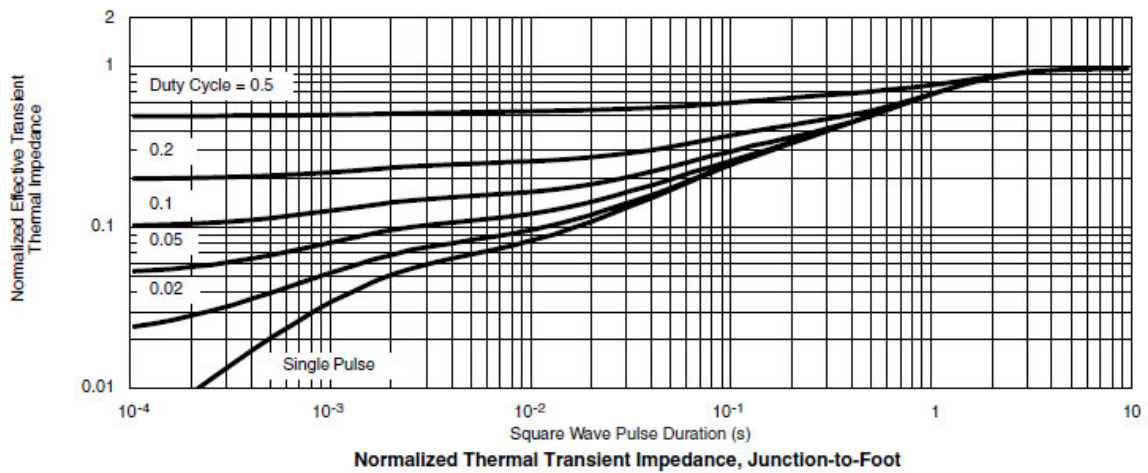
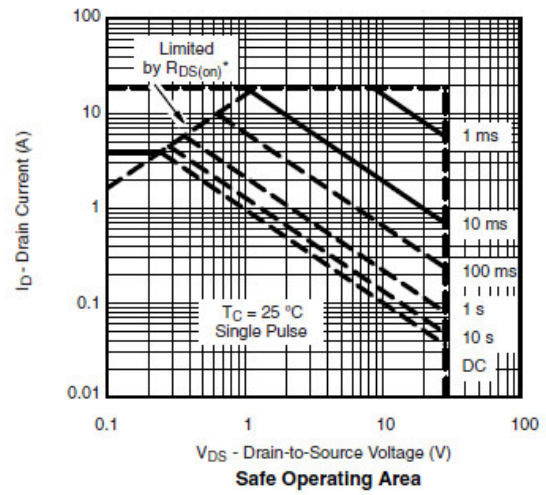
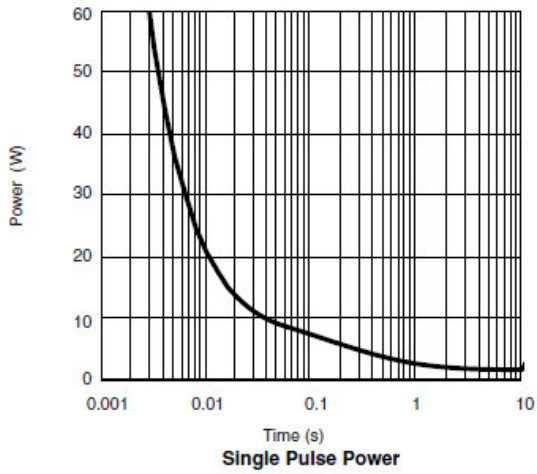
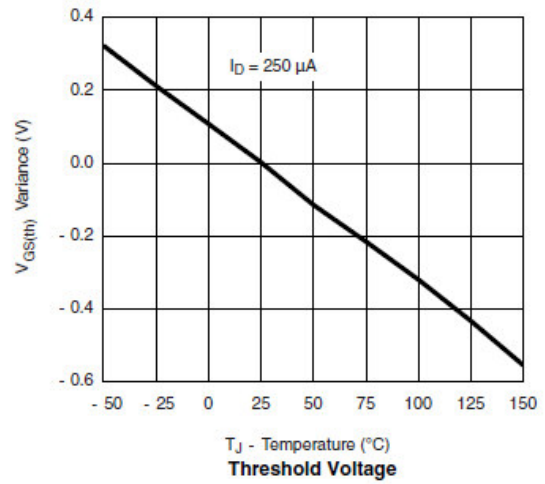
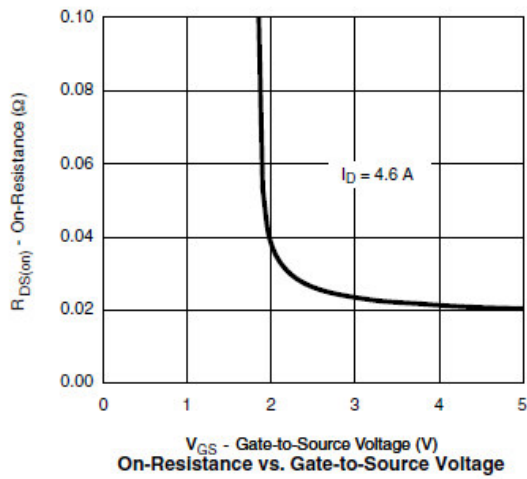
( $T_A=25^\circ\text{C}$  unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
<b>Static</b>						
$V_{(BR)DSS}$	Drain-Source Breakdown Voltage	$V_{GS}=0V, I_D=250\mu A$	20			V
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS}=V_{GS}, I_D=250\mu A$	0.4		1.0	
$I_{GSS}$	Gate Leakage Current	$V_{DS}=0V, V_{GS}=\pm 12V$			$\pm 100$	nA
$I_{DSS}$	Zero Gate Voltage Drain Current	$V_{DS}=16V, V_{GS}=0V$			1	uA
		$V_{DS}=16V, V_{GS}=0V, T_J=85^\circ\text{C}$			30	
$I_{D(on)}$	On-State Drain Current	$V_{DS} \geq 5V, V_{GS}=4.5V$	10			A
$R_{DS(on)}$	Drain-Source On-Resistance	$V_{GS}=4.5V, I_D=6.0A$		20	28	m $\Omega$
		$V_{GS}=2.5V, I_D=5.0A$		23	32	
		$V_{GS}=1.8V, I_D=4.0A$		28	42	
$g_{FS}$	Forward Transconductance	$V_{DS}=5V, I_D=6A$		25		S
$V_{SD}$	Diode Forward Voltage	$I_S=1.6A, V_{GS}=0V$		0.7	1.2	V
<b>Dynamic</b>						
$C_{iss}$	Input Capacitance	$V_{DS}=20V, V_{GS}=0V, f=1\text{MHz}$		700		pF
$C_{oss}$	Output Capacitance			75		
$C_{rSS}$	Reverse Transfer Capacitance			45		
$Q_g$	Total Gate Charge	$V_{DS}=10V, V_{GS}=4.5V, I_D=6.0A$		650		pC
$Q_{gs}$	Gate-Source Charge			200		
$Q_{gd}$	Gate-Drain Charge			180		
$t_{d(on)}$	Turn-On Time	$V_{DD}=10V, R_L=1.4\Omega, I_D=1.0A, V_{GEN}=4.5V, R_G=3\Omega$		8	12	ns
$T_r$				12	20	
$t_{d(off)}$	Turn-Off Time			32	40	
$T_f$				10	15	

## Typical Performance Characteristics

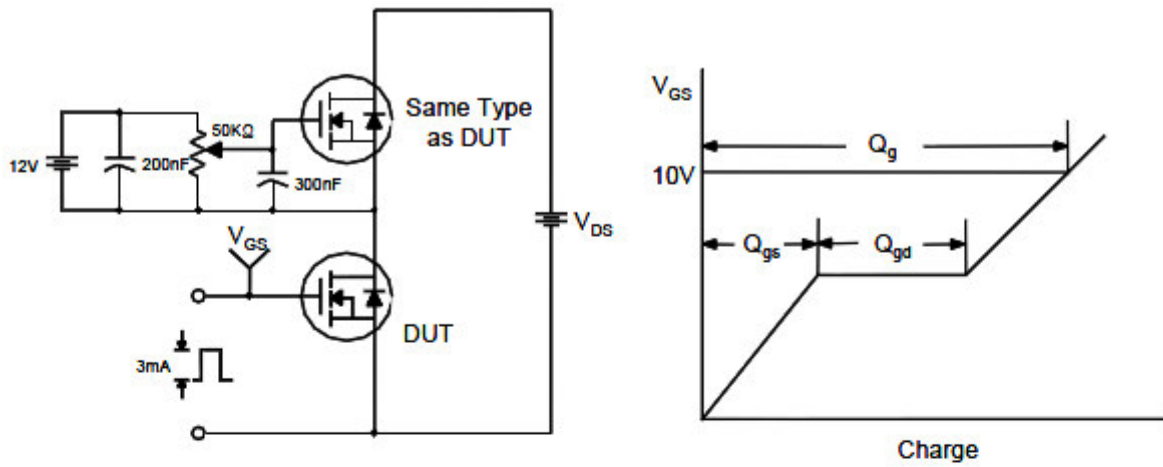


## Typical Performance Characteristics (continue)

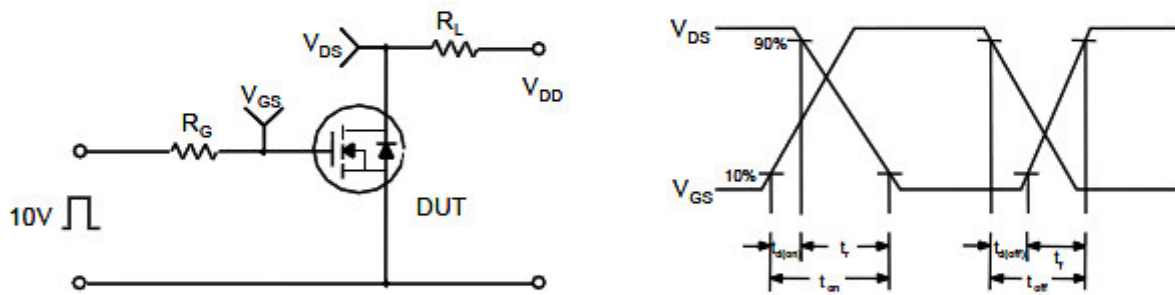


## Typical Characteristics

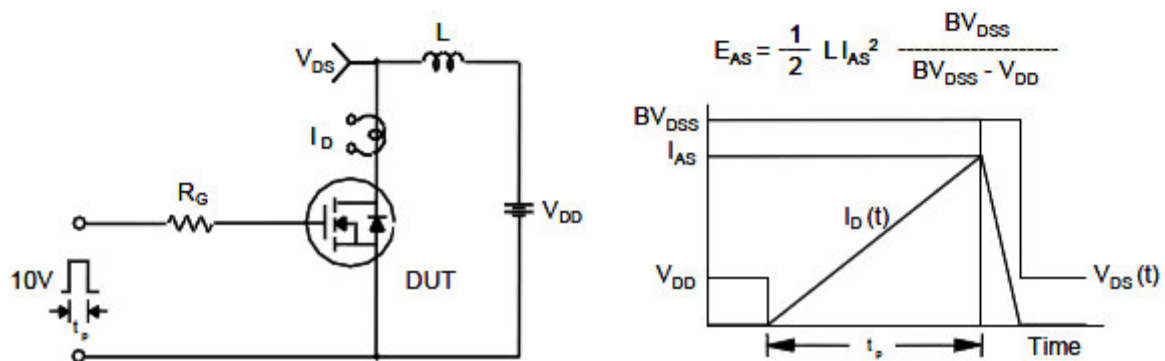
Gate Charge Test Circuit & Waveform



Resistive Switching Test Circuit & Waveforms

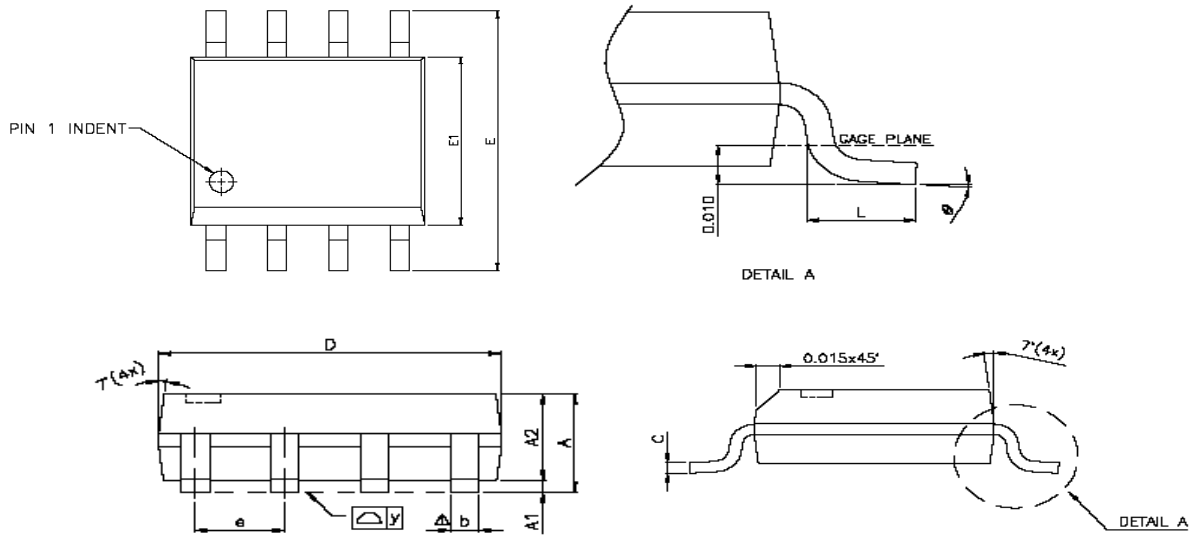


Unclamped Inductive Switching Test Circuit & Waveforms



Package Dimension

# SOP-8P PLASTIC PACKAGE




Dimensions						
SYMBOL	Millimeters			Inches		
	MIN	NOM	MAX	MIN	NOM	MAX
A	1.47	1.60	1.73	0.058	0.063	0.068
A1	0.10	-	0.25	0.004	-	0.010
A2	-	1.45	-	-	0.057	-
b	0.33	0.41	0.51	0.013	0.016	0.020
C	0.19	0.20	0.25	0.0075	0.008	0.0098
D	4.80	4.85	4.95	0.189	0.191	0.195
E	5.80	6.00	6.20	0.228	0.236	0.244
E1	3.80	3.90	4.00	0.150	0.154	0.157
e	-	1.27	-	-	0.050	-
L	0.38	0.71	1.27	0.015	0.028	0.050
$\Delta y$	-	-	0.076	-	-	0.003
$\theta$	0°	-	8°	0°	-	8°



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